





# LVDS 4x4 CROSSPOINT SWITCH

## FEATURES

- Greater Than 2.0 Gbps Operation
- Nonblocking Architecture Allows Each Output to be Connected to Any Input
- Pk-Pk Jitter:
  - 60 ps Typical at 2.0 Gbps
  - 110 ps Typical at 2.5 Gbps
- Compatible With ANSI TIA/EIA-644-A LVDS Standard
- Available Packaging 38-Pin TSSOP
- 25 mV of Input Voltage Threshold Hysteresis
- Propagation Delay Times: 800 ps Typical
- Inputs Electrically Compatible With LVPECL, CML and LVDS Signal Levels
- Operates From a Single 3.3-V Supply
- Low Power: 110 mA Typical
- Integrated 110-Ω Line Termination Resistors Available With SN65LVDT250

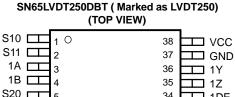
## **APPLICATIONS**

- Clock Buffering/Clock Muxing
- Wireless Base Stations
- High-Speed Network Routing
- Telecom/Datacom

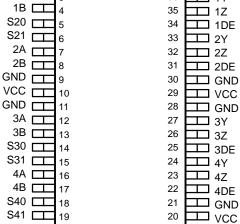
# DESCRIPTION

The SN65LVDS250 and SN65LVDT250 are 4x4 nonblocking crosspoint switches in a flow-through pin-out allowing for ease in PCB layout. Low-voltage differential signaling (LVDS) is used to achieve a high-speed data throughput while using low power. Each of the output drivers includes a 4:1 multiplexer to allow any input to be routed to any output. Internal signal paths are fully differential to achieve the high signaling speeds while maintaining low signal skews. The SN65LVDT250 incorporates  $110-\Omega$  termination resistors for those applications where board space is a premium.

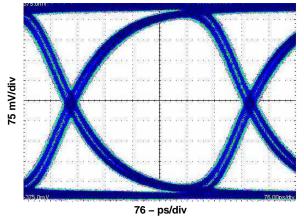
The SN65LVDS250 and SN65LVDT250 are characterized for operation from -40°C to 85°C.



SN65LVDS250DBT (Marked as LVDS250)



## **EYE PATTERN**



 $V_{IC}$ = 1.2 V  $|V_{ID}|$  = 200 mV 2 Gbps Input = PRBS 2<sup>23</sup> -1  $V_{CC}$  = 3.3 V



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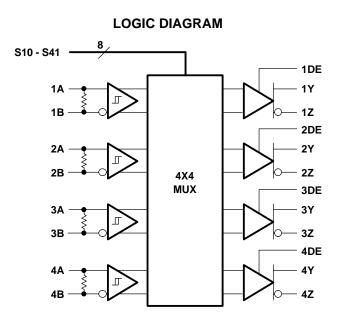
## SN65LVDS250 **SN65LVDT250**





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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.



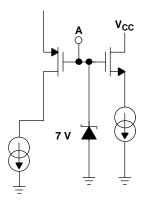
Integrated Termination on LVDT Only

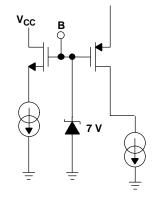


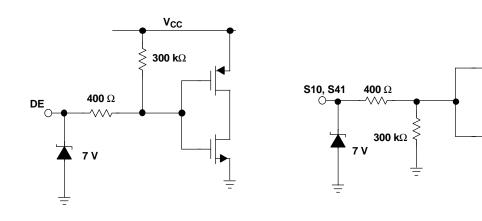
Vcc

## EQUIVALENT INPUT AND OUTPUT SCHEMATIC DIAGRAMS

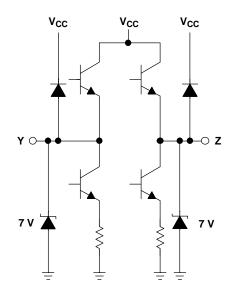
**INPUT LVDS250** 







**OUTPUT LVDS250** 



#### Table 1. CROSSPOINT LOGIC TABLES

Ol	OUTPUT CHANNEL 1			OUTPUT CHANNEL 2			JTPUT CH	IANNEL 3	OUTPUT CHANNEL 4		
	TROL NS	INPUT SELECTED		TROL NS	INPUT SELECTED		TROL NS	INPUT SELECTED		TROL NS	INPUT SELECTED
S10	S11	1Y/1Z	S20	S21	2Y/2Z	S30	S31	3Y/3Z	S40	S41	4Y/4Z
0	0	1A/1B	0	0	1A/1B	0	0	1A/1B	0	0	1A/1B
0	1	2A/2B	0	1	2A/2B	0	1	2A/2B	0	1	2A/2B
1	0	3A/3B	1	0	3A/3B	1	0	3A/3B	1	0	3A/3B
1	1	4A/4B	1	1	4A/4B	1	1	4A/4B	1	1	4A/4B

#### PACKAGE DISSIPATION RATINGS

PACKAGE	PACKAGE CIRCUIT BOARD MODEL		DERATING FACTOR <sup>(1)</sup> ABOVE $T_A = 25^{\circ}C$	T <sub>A</sub> = 85°C POWER RATING
TSSOP (DBT)	Low-K <sup>(2)</sup>	1038 mW	9.0 mW/°C	496 mW
TSSOP (DBT)	High-K <sup>(3)</sup>	1772 mW	15.4 mW/°C	847 mW

(1) This is the inverse of the junction-to-ambient thermal resistance when board-mounded and with no air flow.

(2) In accordance with the Low-K thermal metric definitions of EIA/JESD51-6

(3) In accordance with the High-K thermal metric definitions of EIA/JESD51-6

### THERMAL CHARACTERISTICS

	PARAMETER	TEST CONDITIONS	VALUE	UNITS
$\Theta_{JB}$	Junction-to-board thermal resistance		40.3	°C/W
$\Theta_{JC}$	Junction-to-case thermal resistance		8.5	C/VV
<b>_</b>	Device newer dissinction	$V_{CC} = 3.3 \text{ V}, \text{ T}_{A} = 25^{\circ}\text{C}, 1 \text{ GHz}$	356	mW
P <sub>D</sub> Device power dissipation	Device power dissipation	$V_{CC} = 3.6 \text{ V}, \text{ T}_{A} = 85^{\circ}\text{C}, 1 \text{ GHz}$	522	mW

## **ABSOLUTE MAXIMUM RATINGS**

over operating free-air temperature range unless otherwise noted<sup>(1)</sup>

			UNITS				
Supply voltage range, $V_{CC}$			-0.5 V to 4 V				
	S, DE		-0.5 V to 4 V				
Valtaga ranga(2)	А, В		-0.5 V to 4 V				
Voltage range <sup>(2)</sup>	V <sub>A</sub> - V <sub>B</sub>   (LVDT only)	V <sub>A</sub> - V <sub>B</sub>   (LVDT only)					
	Y, Z	Y, Z					
Electrostatio discharge	Human body model <sup>(3)</sup>	All pins	±3 kV				
Electrostatic discharge	Charged-device model <sup>(4)</sup>	All pins	±500 V				
Continuous power dissipation	1		See Dissipation Rating Table				

(1) Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) All voltage values, except differential I/O bus voltages, are with respect to network ground terminal.

(3) Tested in accordance with JEDEC Standard 22, Test Method A114-A.

(4) Tested in accordance with JEDEC Standard 22, Test Method C101.



## **RECOMMENDED OPERATING CONDITIONS**

			MIN	NOM	MAX	UNIT
V <sub>CC</sub>	Supply voltage		3	3.3	3.6	V
V <sub>IH</sub>	High-level input voltage	S10-S41, 1DE-4DE	2		$V_{CC}$	V
V <sub>IL</sub>	Low-level input voltage	S10-S41, 1DE-4DE	0		0.8	V
NZ 1	Magnitude of differential input voltage	LVDS	0.1		1	V
V <sub>ID</sub>	Magnitude of differential input voltage	LVDT	0.1	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	V	
	Input voltage (any combination of common	-mode or input signals)	0		3.3	V
TJ	Junction temperature				140	°C
T <sub>A</sub> <sup>(1)</sup>	Operating free-air temperature		-40		85	°C

(1) Maximum free-air temperature operation is allowed as long as the device maximum junction temperature is not exceeded.

## TIMING SPECIFICATIONS

		PARAMETER	MIN	NOM	MAX	UNIT
t <sub>SET</sub>	Input to select setup time			0.6		ns
t <sub>HOLD</sub>	Input to select hold time	See Figure 7		0.2		ns
t <sub>SWITCH</sub>	Select to switch output			1.2	1.6	ns

## INPUT ELECTRICAL CHARACTERISTICS

over recommended operating conditions unless otherwise noted<sup>(1)</sup>

	PARAMETER		TEST CONDITIONS	MIN	<b>TYP</b> <sup>(1)</sup>	MAX	UNIT
V <sub>IT+</sub>	Positive-going differential input voltage	e threshold	See Figure 1			100	mV
V <sub>IT-</sub>	Negative-going differential input voltage	e threshold	See Figure 1	-100			mV
V <sub>ID(HYS)</sub>	Differential input voltage hysteresis				25		mV
		1DE-4DE	<u>и а</u> у	-10			
IIH	High-level input current	S10-S41	$V_{IH} = 2 V$			20	μA
	Law level level and an end	1DE-4DE		-10			
IIL	Low-level input current	S10-S41	$V_{IL} = 0.8 V$			20	μA
I <sub>I</sub>	Input current (A or B inputs)		$V_I = 0$ V or 3.3 V, second input at 1.2 V (other input open for LVDT)	-20		20	μA
I <sub>I(OFF)</sub>	Input current (A or B inputs)		$V_{CC} \le 1.5 \text{ V}, \text{ V}_{I} = 0 \text{ V} \text{ or } 3.3 \text{ V}, \text{ second}$ input at 1.2 V(other input open for LVDT)	-20		20	μA
I <sub>IO</sub>	Input offset current ( I <sub>IA</sub> - I <sub>IB</sub>  ) (LVDS)		$V_{IA} = V_{IB}$ , $0 \le V_{IA} \le 3.3$ V	-6		6	μA
	Termination resistance (LVDT)		$V_{ID} = 300 \text{ mV}, V_{IC} = 0 \text{ V to } 3.3 \text{ V}$	90	110	132	
R <sub>T</sub>			$V_{ID} = 300 \text{ mV}, V_{IC} = 0 \text{ V to } 3.3 \text{ V}, V_{CC} = 1.5 \text{ V}$	90	110	132	Ω
CI	Differential input capacitance				2.5		pF

(1) All typical values are at  $25^{\circ}$ C and with a 3.3 V supply.



## **OUTPUT ELECTRICAL CHARACTERISTICS**

over recommended operating conditions unless otherwise noted

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
V <sub>OD</sub>	Differential output voltage magnitude	See Figure 2	247	350	454	mV
$\Delta  V_{OD} $	Change in differential output voltage magnitude between logic states	$V_{ID} = \pm 100 \text{ mV}$	-50		50	mV
V <sub>OC(SS)</sub>	Steady-state common-mode output voltage		1.125		1.375	V
$\Delta V_{OC(SS)}$	Change in steady-state common-mode output voltage between logic states	See Figure 3	-50		50	mV
V <sub>OC(PP)</sub>	Peak-to-peak common-mode output voltage			50	150	mV
I <sub>CC</sub>	Supply current	R <sub>L</sub> =100 Ω		110	145	mA
I <sub>OS</sub>	Short-circuit output current	$V_{OY}$ or $V_{OZ}$ = 0 V	-27		27	mA
I <sub>OSD</sub>	Differential short circuit output current	$V_{OD} = 0 V$	-12		12	mA
I <sub>oz</sub>	High-impedance output current	$V_{O} = 0 V \text{ or } V_{CC}$			±1	μA
Co	Differential output capacitance			2		pF

## SWITCHING CHARACTERISTICS

over recommended operating conditions unless otherwise noted

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t <sub>PLH</sub>	Propagation delay time, low-to-high-level output		700	800	1200	
t <sub>PHL</sub>	Propagation delay time, high-to-low-level output	See Figure 4	700	800	1200	
t <sub>r</sub>	Differential output signal rise time (20%-80%)	See Figure 4		200	245	ps
t <sub>f</sub>	Differential output signal fall time (20%-80%)			200	245	
t <sub>sk(p)</sub>	Pulse skew ( t <sub>PHL</sub> - t <sub>PLH</sub>  ) <sup>(1)</sup>			0	50	ps
t <sub>sk(o)</sub>	Channel-to-channel output skew <sup>(2)</sup>				175	ps
t <sub>sk(pp)</sub>	Part-to-part skew <sup>(3)</sup>				300	ps
t <sub>jit(per)</sub>	Period jitter, rms (1 standard deviation) <sup>(4)</sup>	See Figure 6		1	3	ps
t <sub>jit(cc)</sub>	Cycle-to-cycle jitter (peak) <sup>(5)</sup>	See Figure 6		8	17	ps
t <sub>jit(pp)</sub>	Peak-to-peak jitteR <sup>(6)</sup>	See Figure 6		60	110	ps
t <sub>jit(det)</sub>	Deterministic jitter, peak-to-peak <sup>(7)</sup>	See Figure 6		48	65	ps
t <sub>PHZ</sub>	Propagation delay, high-level-to-high-impedance output				6	
t <sub>PLZ</sub>	Propagation delay, low-level-to-high-impedance output	Coo Figure 5			6	
t <sub>PZH</sub>	Propagation delay, high-impedance -to-high-level output	See Figure 5			300	ns
t <sub>PZL</sub>	Propagation delay, high-impedance-to-low-level output				300	

(1)  $t_{sk(p)}$  is the magnitude of the time difference between the  $t_{PLH}$  and  $t_{PHL}$  of any output of a single device.

 $t_{sk(o)}$  is the maximum delay time difference between drivers over temperature, V<sub>CC</sub>, and process. (2)

 $t_{sk(o)}$  is the magnitude of the difference between divers over temperature,  $v_{CC}$ , and process.  $t_{sk(pp)}$  is the magnitude of the difference in propagation delay times between any specified terminals of two devices when both devices operate with the same supply voltages, at the same temperature, and have identical packages and test circuits. Input voltage =  $V_{ID}$  = 200 mV, 50% duty cycle at 1.0 GHz,  $t_r = t_f = 50$  ps (20% to 80%), measured over 1000 samples. Input voltage =  $V_{ID}$  = 200 mV, 50% duty cycle at 1.0 GHz,  $t_r = t_f = 50$  ps (20% to 80%). Input voltage =  $V_{ID}$  = 200 mV, 2<sup>23</sup>-1 PRBS pattern at 2.0 Gbps,  $t_r = t_f = 50$  ps (20% to 80%), measured over 200k samples. Input voltage =  $V_{ID}$  = 200 mV, 2<sup>7</sup>-1 PRBS pattern at 2.0 Gbps,  $t_r = t_f = 50$  ps (20% to 80%). (3)

(4)

(5)

(6)

(7)

#### PARAMETER MEASUREMENT INFORMATION

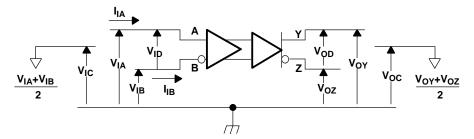


Figure 1. Voltage and Current Definitions

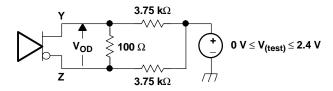
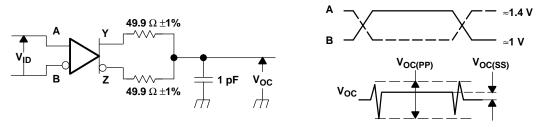
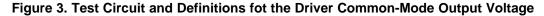
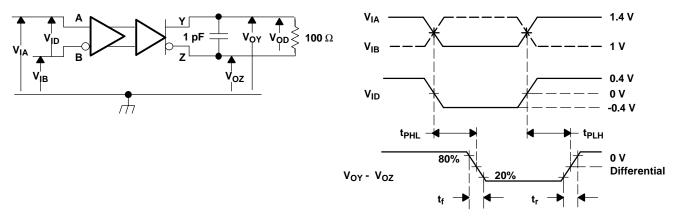


Figure 2. Differential Output Voltage (V<sub>OD</sub>) Test Circuit



A. All input pulses are supplied by a generator having the following characteristics:  $t_r$  or  $t_f \le 1$  ns, pulse-repetition rate (PRR) = 0.5 Mpps, pulse width = 500 ±10 ns;  $R_L = 100\Omega$ ;  $C_L$  includes instrumentation and fixture capacitance within 0,06 mm of the DUT; the measurement of  $V_{OC(PP)}$  is made on test equipment with a -3 dB bandwidth of at least 300 MHz.

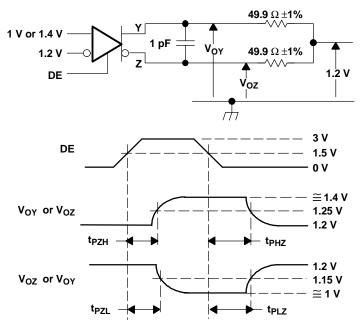




A. All input pulses are supplied by a generator having the following characteristics: t<sub>r</sub> or t<sub>f</sub>≤ 0.25 ns, pulse-repetition rate (PRR) = 0.5 Mpps, pulse width = 500 ± 10 ns . C<sub>L</sub> includes instrumentation and fixture capacitance within 0,06 mm of the DUT.

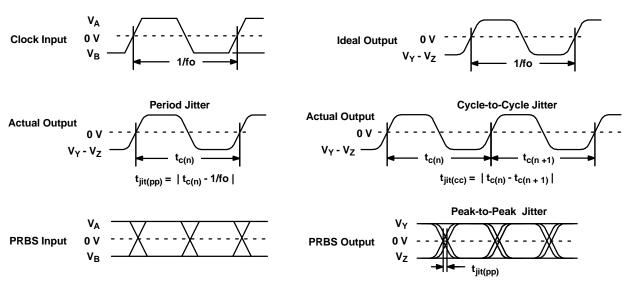
Figure 4. Timing Test Circuit and Waveforms

#### PARAMETER MEASUREMENT INFORMATION (continued)



A. All input pulses are supplied by a generator having the following characteristics:  $t_r$  or  $t_r \le 1$  ns, pulse-repetition rate (PRR) = 0.5 Mpps, pulse width = 500 ± 10 ns.  $C_L$  includes instrumentation and fixture capacitance within 0,06 mm of the DUT.

Figure 5. Enable and Disable Time Circuit and Definitions

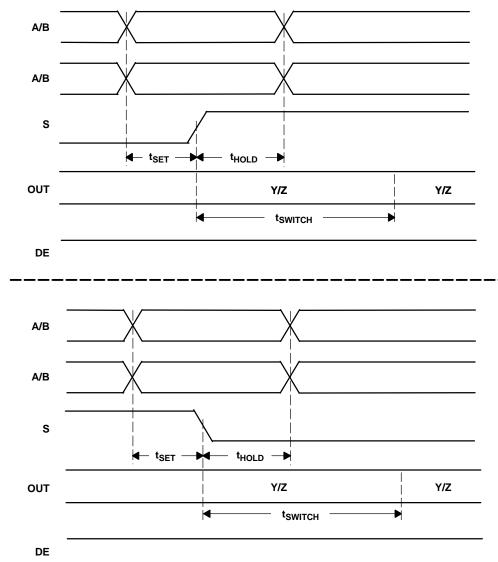


A. All input pulses are supplied by an Agilent 81250 Stimulus System.

B. The measurement is made on a TEK TDS6604 running TDSJIT3 application software.

Figure 6. Driver Jitter Measurement Waveforms

## PARAMETER MEASUREMENT INFORMATION (continued)

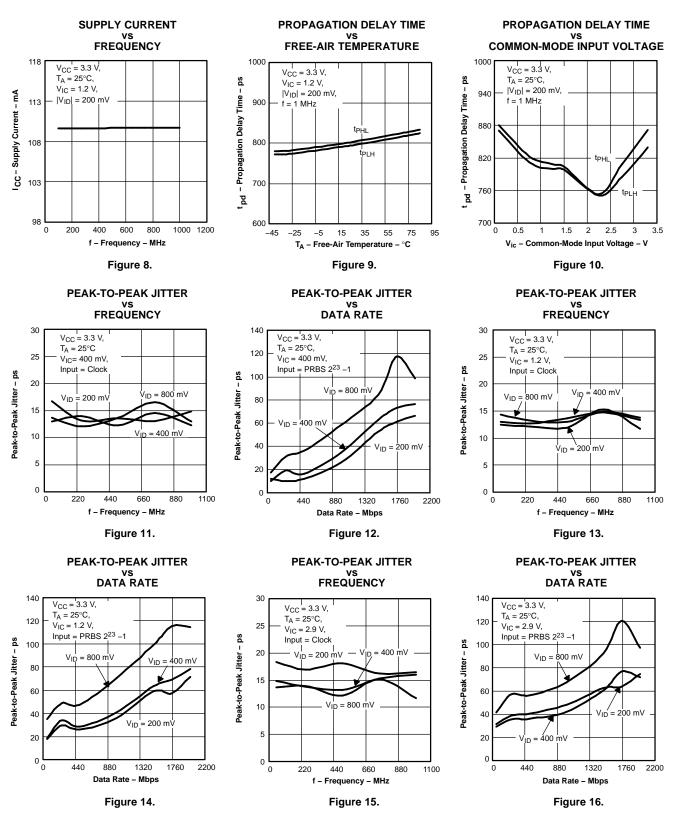


A. t<sub>SET</sub> and t<sub>HOLD</sub> times specify that data must be in a stable state before and after mux control switches.

Figure 7. Input to Select for Both Rising and Falling Edge Setup and Hold Times



### **TYPICAL CHARACTERISTICS**



## **TYPICAL CHARACTERISTICS (continued)**

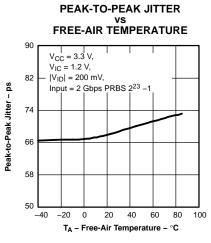
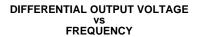
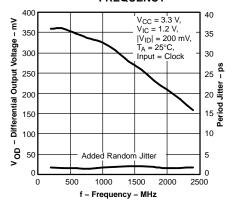
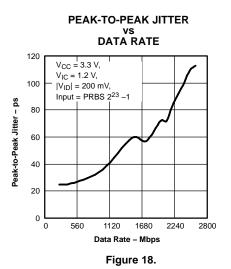


Figure 17.

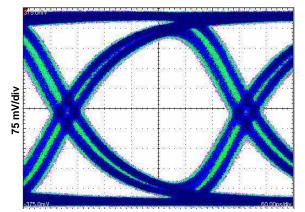






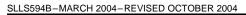


EYE PATTERN



 $\label{eq:VIC} \begin{array}{l} 60-ps/div \\ V_{IC}{=}\;1.2~V, \, |V_{ID}| = 200~mV, \, 2.5~Gbps, \\ Input = PRBS\;2^{23}-1, \, V_{CC}{=}\;3.3~V \end{array}$ 

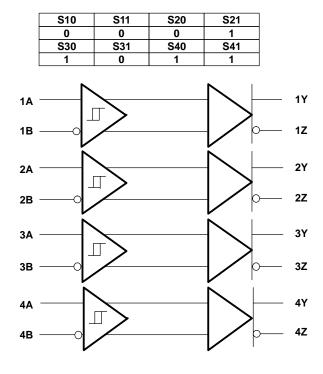
Figure 20.

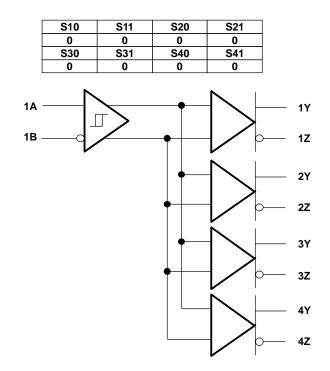


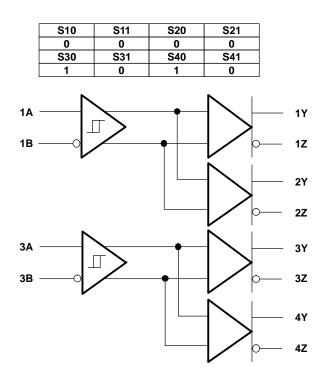


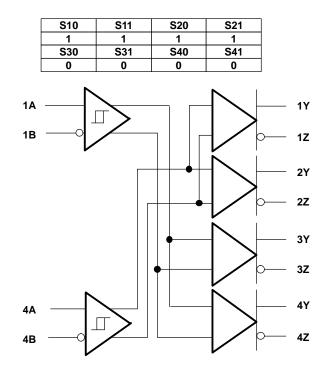
#### **APPLICATION INFORMATION**

## **CONFIGURATION EXAMPLES**







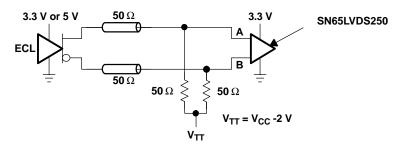


SN65LVDS250 SN65LVDT250

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### APPLICATION INFORMATION (continued)

**TYPICAL APPLICATION CIRCUITS (ECL, PECL, LVDS, etc.)** 





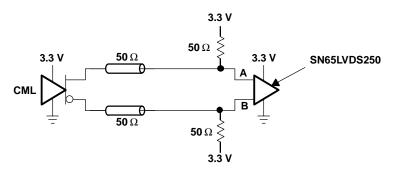


Figure 22. Current-Mode Logic (CML)

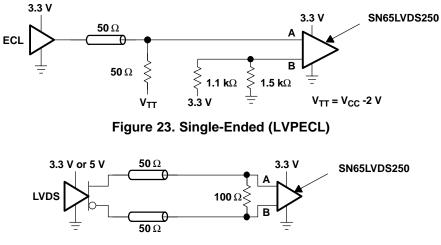


Figure 24. Low-Voltage Differential Signaling (LVDS)



## **PACKAGING INFORMATION**

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
SN65LVDS250DBT	(1) ACTIVE	TSSOP	DBT	38	50	(2) Green (RoHS & no Sb/Br)	(6) CU NIPDAU	(3) Level-2-260C-1 YEAR	-40 to 85	(4/5) LVDS250	Samples
SN65LVDS250DBTR	ACTIVE	TSSOP	DBT	38	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	LVDS250	Samples
SN65LVDS250DBTRG4	ACTIVE	TSSOP	DBT	38	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	LVDS250	Samples
SN65LVDT250DBT	ACTIVE	TSSOP	DBT	38	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	LVDT250	Samples
SN65LVDT250DBTR	ACTIVE	TSSOP	DBT	38	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	LVDT250	Samples

<sup>(1)</sup> The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

<sup>(2)</sup> RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

**RoHS Exempt:** TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

**Green:** TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

<sup>(3)</sup> MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

<sup>(4)</sup> There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

<sup>(5)</sup> Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

<sup>(6)</sup> Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.



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24-Aug-2018

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# PACKAGE MATERIALS INFORMATION

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## TAPE AND REEL INFORMATION





## QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal												
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN65LVDS250DBTR	TSSOP	DBT	38	2000	330.0	16.4	6.9	10.2	1.8	12.0	16.0	Q1
SN65LVDT250DBTR	TSSOP	DBT	38	2000	330.0	16.4	6.9	10.2	1.8	12.0	16.0	Q1

TEXAS INSTRUMENTS

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# PACKAGE MATERIALS INFORMATION

26-Feb-2019

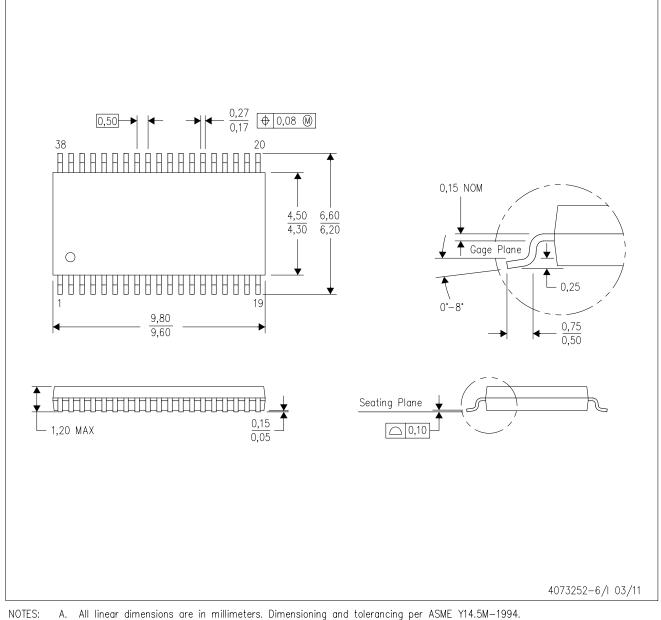


\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN65LVDS250DBTR	TSSOP	DBT	38	2000	350.0	350.0	43.0
SN65LVDT250DBTR	TSSOP	DBT	38	2000	350.0	350.0	43.0

DBT (R-PDSO-G38)

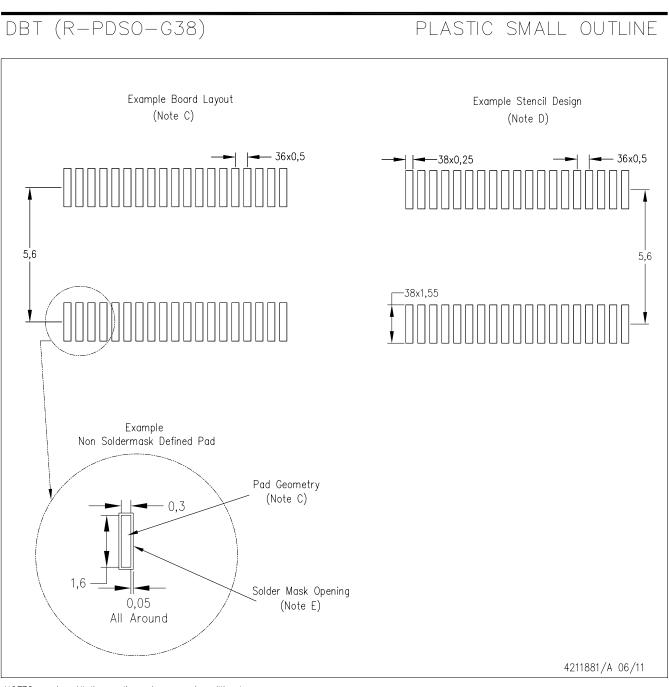
PLASTIC SMALL OUTLINE



B. This drawing is subject to change without notice.

- C. Body dimensions do not include mold flash or protrusion.
- D. Falls within JEDEC MO-153.





- NOTES: A. All linear dimensions are in millimeters.
  - B. This drawing is subject to change without notice.
  - C. Publication IPC-7351 is recommended for alternate designs
  - D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525.
  - E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



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